CLAIMS

1. A ~~Method~~ method for fabricating a re-built wafer ~~(100) which comprises~~ comprising chips ~~(1)~~ having connection pads ~~(10), this~~ the method comprising ~~the following steps of~~:

- fabricating a first wafer of chips ~~(1)~~,

~~characterized in that it also comprises the following steps:~~

~~production~~ producing, on ~~this~~ the first wafer, ~~of~~ a stack of at least one layer of redistribution of ~~the~~ pads ~~(10)~~ of the chips on conductive tracks ~~(12)~~ joining the pads to an exposed side periphery of the chips and designed for ~~the~~ interconnection of the chips, ~~this~~ the stack being designated ~~the~~ a main RDL layer ~~(14)~~,

- cutting ~~this~~ the first wafer ~~in order~~ to obtain individual chips ~~(1)~~, each ~~furnished with their~~ individual chip including its main RDL layer ~~(14)~~,

- transferring the individual chips with their main RDL layer ~~(14)~~ to a sufficiently rigid support ~~(20)~~ to remain flat during the following steps, ~~which~~ the rigid support ~~is furnished with~~ including an adhesive layer ~~(21), with~~ the main RDL layer ~~(14) on~~ being over the adhesive layer ~~(21)~~,

- depositing a resin ~~(30) in order~~ over the individual chips to encapsulate the individual chips ~~(1)~~,

- polymerizing the resin,

- removing the rigid support ~~(20)~~, and

- depositing a single redistribution layer ~~called~~ designated a mini RDL ~~(24) in order~~ layer to connect the conductive tracks of the main RDL layer ~~(14) up~~ to interconnection contacts, through apertures ~~(22)~~ made in the adhesive layer ~~(21)~~, such that the re-built wafer ~~comprising~~ comprises the polymerized resin, and the

chips with their main RDL layer and their mini RDL ~~being the re-built wafer (100)~~ layer.

2. ~~The Method~~ method for fabricating ~~a~~ the re-built wafer ~~(100)~~ according to ~~the preceding~~ claim 1, ~~characterized in that it also comprises a step of~~ further comprising testing ~~and/or of burning in of the chips (1) before they are transferred~~ the individual chips before transferring the individual chips to the rigid support ~~(20)~~.

3. ~~The Method~~ method ~~of~~ for fabricating ~~a~~ the re-built wafer ~~(100)~~ according to ~~either one of the preceding~~ claims 1, ~~characterized in that~~ wherein the apertures ~~(22)~~ in the adhesive layer ~~(21)~~ are made before transferring the individual chips to the rigid support.

4. ~~The Method~~ method ~~of~~ for fabricating ~~a~~ the re-built wafer ~~(100)~~ according to claim 1 ~~or 2, characterized in that~~ wherein the apertures ~~(22)~~ in the adhesive layer ~~(21)~~ are made after ~~the step of~~ removing the rigid support.

5. ~~The Method~~ method ~~of~~ for fabricating ~~a~~ the re-built wafer ~~(100)~~ according to ~~any one of the preceding~~ claims 1, ~~characterized in that the~~ wherein conductors ~~(23)~~ of the mini RDL ~~(24)~~ layer are in the form of a T or a Latin cross.

6. ~~The Method~~ method ~~of~~ for fabricating ~~a~~ the re-built wafer ~~(100)~~ according to ~~any one of the preceding~~ claims 1, ~~characterized in that~~ wherein the adhesive layer ~~(21)~~ is ~~in~~ made of an irreversible bonding material.

7. The method for fabricating the re-built wafer according to claim 1, further comprising burning-in the individual chips before transferring the individual chips to the rigid support.

8. The method for fabricating the re-built wafer according to claim 1, wherein the exposed side periphery of the chips is perpendicular to the stack of the at least one layer of redistribution of pads of the chips.